Analog Engineer's

Pocket Reference

Art Kay and Tim Green, Editors

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Analog Engineer's Pocket Reference

Third Edition

Edited by:

Art Kay and Tim Green

Special thanks for technical contribution and review: Kevin Duke Rafael Ordonez John Caldwell Collin Wells Ian Williams Thomas Kuehl

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Message from the editors:

This pocket reference is intended as a valuable quick guide for often used board- and systemlevel design formulae. This collection of formulae is based on a combined 50 years of analog board- and system-level expertise. Much of the material herein was referred to over the years via a folder stuffed full of printouts. Those worn pages have been organized and the information is now available via this guide in a bound and hard-to-lose format!

Here is a brief overview of the key areas included:

- · Key constants and conversions
- Discrete components
- AC and DC analog equations
- Op amp basic configurations
- OP amp bandwidth and stability
- Overview of sensors
- PCB trace R, L, C
- Wire L, R, C
- Binary, hex and decimal formats
- A/D and D/A conversions

We hope you find this collection of formulae as useful as we have. Please send any comments and/or ideas you have for the next edition of the *Analog Engineer's Pocket Reference* to **artkay_timgreen@list.ti.com**

Additional resources:

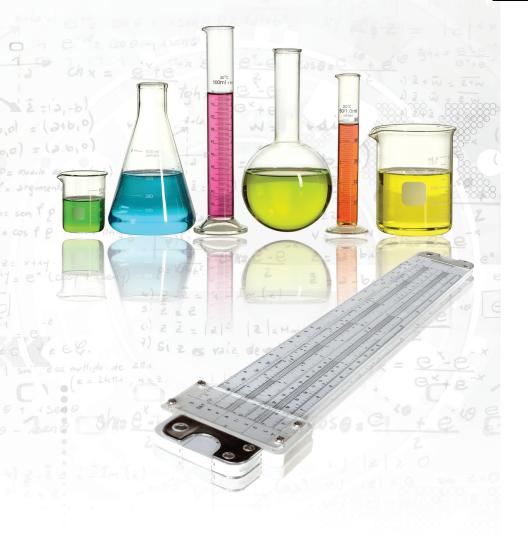
- Search for complete board-and-system level circuits in the TI Designs Precision reference design library (www.ti.com/precisiondesigns).
- Read how-to blogs from TI precision analog experts at the Precision Hub (www.ti.com/thehub).
- Find solutions, get help, share knowledge and solve problems with fellow engineers and TI experts in the TI E2E[™] Community (www.ti.com/e2e).

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	-

Conversions

- Standard decimal prefixes
- Metric conversions
- Temperature scale conversions
- Error conversions (ppm and percentage)



7

Conversions

Table 1: Physical constants

Constant	Symbol	Value 3.00×10^8 8.85×10^{-12} 1.26×10^{-6}	Units
Speed of light in a vacuum	c		m/s
Permittivity of vacuum	ε _ο		F/m
Permeability of free space	μ _ο		H/m
Plank's constant	h	6.63 x 10 ⁻³⁴	Js
Boltzmann's constant	k	1.38 x 10 ⁻²³	J/K
Faraday's constant	F	9.65 x 10 ⁴	C/mol
Avogadro's constant	N _A	6.02 x 10 ²³	/mol
Unified atomic mass unit	m _u	1.66 x 10 ⁻²⁷	kg
Electronic charge	q	1.60 x 10 ⁻¹⁹	C
Rest mass of electron	m _e	9.11 x 10 ⁻³¹	kg
Mass of proton	m _p	1.67 x 10 ⁻²⁷	kg
Gravitational constant	G	6.67 x 10 ⁻¹¹	Nm²/kg
Standard gravity	g _n	9.81	m/s²
Ice point	T _{ice}	273.15	K
Maximum density of water	ρ	1.00 x 10 ³	kg/m³
Density of mercury	Рнд	1.36 x 10 ⁴	kg/m ³
Gas constant	R	8.31	J/(K•mol)
Speed of sound in air (at 273 K)	C _{air}	3.31 x 10 ²	m/s

Multiplier	Prefix	Abbreviation
10 ¹²	tera	Т
10 ⁹	giga	G
10 ⁶	mega	M
10 ³	kilo	k
10 ⁻³	milli	m
10 ⁻⁶	micro	μ
10 ⁻⁹	nano	n
10 ⁻¹²	pico	р
10 ⁻¹⁵	femto	f
10 ⁻¹⁸	atto	а

Table 2: Standard decimal prefixes

Table 3: English to metric conversions

Unit	Symbol	Equivalent	Unit	Symbol
inches	in	25.4 mm/in	millimeter	mm
mil	mil	0.0254 mm/mil	millimeter	mm
feet	ft	0.3048 m/ft	meters	m
yards	yd	0.9144 m/yd	meters	m
miles	mi	1.6093 km/mi	kilometers	km
circular mil	cir mil	5.067x10 ⁻⁴ mm ² /cir mil	square millimeters	mm ²
square yards	yd ²	0.8361 m ²	square meters	m²
pints	pt	0.5682 L/pt	liters	L
ounces	oz	28.35 g/oz	grams	g
pounds	lb	0.4536 kg/lb	kilograms	kg
calories	cal	4.184 J/cal	joules	J
horsepower	hp	745.7 W/hp	watts	W

Table 4: Metric to English conversions

Unit	Symbol	Conversion	Unit	Symbol
millimeter	mm	0.0394 in/mm	inch	in
millimeter	mm	39.4 mil/mm	mil	mil
meters	m	3.2808 ft/m	feet	ft
meters	m	1.0936 yd/m	yard	yd
kilometers	km	0.6214 mi/km	miles	mi
square millimeters	mm ²	1974 cir mil/mm ²	circular mil	cir mil
square meters	m²	1.1960 yd²/ m²	square yards	yd ²
liters	L	1.7600 pt/L	pints	pt
grams	g	0.0353 oz/g	ounces	oz
kilograms	kg	2.2046 lb/kg	pounds	lb
joules	J	0.239 cal/J	calories	cal
watts	W	1.341x10 ⁻³ hp/W	horsepower	hp

Example

Convert 10 mm to mil.

Answer

 $10 \text{ mm} \times 39.4 \frac{\text{mil}}{\text{mm}} = 384 \text{ mil}$

Conversions

Table 5: Temperature conversions

$^{\circ}\mathrm{C} = \frac{5}{9}(^{\circ}\mathrm{F} - 32)$	Fahrenheit to Celsius
$^{\circ}\mathrm{F} = \frac{9}{5}(^{\circ}\mathrm{C}) + 32$	Celsius to Fahrenheit
K = °C + 273.15	Celsius to Kelvin
$^{\circ}C = K - 273.15$	Kelvin to Celsius

Table 6: Error conversions

$Error(\%) = \frac{Measured - Ideal}{Ideal} \times 100$	Error in measured value
$Error(\% FSR) = \frac{Measured - Ideal}{Full-scale range} \times 100$	Error in percent of full-scale range
$\% = \frac{\text{ppm}}{10^6} \times 100$	Part per million to percent
$m\% = \frac{ppm}{10^6} \times 100 \times 1000$	Part per million to milli-percent
$ppm = \% \times 10^4$	Percent to part per million
$ppm = m\% \times 10$	Milli-percent to part per million

Example

Compute the error for a measured value of 0.12V when the ideal value is 0.1V and the range is 5V.

Answer

$\text{Error}(\%) = \frac{0.12\text{V} - 0.1\text{V}}{0.1\text{V}} \times 100 = 20\%$	Error in measured value
Error(% FSR) = $\frac{0.12 - 0.1V}{5V} \times 100 = 0.4\%$	Percent FSR

Example

Convert 10 ppm to percent and milli-percent.

Answer

 $\frac{10 \text{ ppm}}{10^6} \times 100 = 0.001\%$ Part per million to percent $\frac{10 \text{ ppm}}{10^6} \times 100 \times 1000 = 1 \text{ m\%}$ Part per million to milli-percent

JF/16V

FEE

T 8 IC3

Resistor color code

12

IC1 TL494

20-0008

94

9

8

- Standard resistor values
- Capacitance specifications
- Capacitance type overview
- Standard capacitance values
- Capacitance marking and tolerance

7015

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FUWERGOOD

Table 7: Resistor color code

Color	Digit	Additional Zeros	Tolerance
None	-na-	-na-	20%
Silver	-na-	-2	10%
Gold	-na-	-1	5%
Black	0	0	
Brown	1	1	
Red	2	2	2%
Orange	3	3	
Yellow	4	4	
Green	5	5	
Blue	6	6	
Violet	7	7	
Grey	8		
White	9		

Example

Yellow, violet, orange and silver indicate 4, 7, and 3 zeros. or a 47 k Ω , 10% resistor.

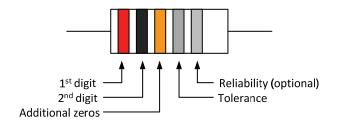


Figure 1: Resistor color code

=	Tab	le	8: S	tan	da	rd	re	si	ste	Y '	va	ue	s																							_
\equiv	[%	5% 10%	68								75								82								91								
\equiv		Ň	9 û	1																																
			1%	68.1		69.8		71.5		73.2		75.0		76.8		78.7		80.6		82.5		84.5		86.6		88.7		90.9		93.1		95.3		97.6		
		0.1%	0.25%	68.1	69.0	69.8	70.6	71.5	72.3	73.2	74.1	75.0	75.9	76.8	77.7	78.7	79.6	80.6	81.6	82.5	83.5	84.5	85.6	86.6	87.6	88.7	89.8	90.9	92.0	93.1	94.2	95.3	96.5	97.6	98.8	
		2%	5% 10%		47							51								56								62								
	cade		1%	46.4		47.5		48.7		49.9		51.1		52.3		53.6		54.9		56.2		57.6		59.0		60.4		61.9		63.4		64.9		66.5		
	00 de	0.1%	0.25% 0.5%	46.4	47.0	47.5	48.1	48.7	49.3	49.9	50.5	51.1	51.7	52.3	53.0	53.6	54.2	54.9	55.6	56.2	56.9	57.6	58.3	59.0	59.7	60.4	61.2	61.9	62.6	63.4	64.2	64.9	65.7	66.5	67.3	
	t o 1	2%	5% 10%					33							36							39								43						
	he 10		1%	31.6		32.4		33.2		34.0		34.8		35.7		36.5		37.4		38.3		39.2		40.2		41.2		42.2		43.2		44.2		45.3		
	Standard resistance values for the 10 to 100 decade	0.1%	0.25%	31.6	32.0	32.4	32.8	33.2	33.6	34.0	34.4	34.8	35.2	35.7	36.1	36.5	37.0	37.4	37.9	38.3	38.8	39.2	39.7	40.2	40.7	41.2	41.7	42.2	42.7	43.2	43.7	44.2	44.8	45.3	45.9	
	/alue	2%	5% 10%			22							24										27									30				
	ance v		1%	21.5		22.1		22.6		23.2		23.7		24.3		24.9		25.5		26.1		26.7		27.4		28.0		28.7		29.4		30.1		30.9		
	esista	0.1%	0.5%	21.5	21.8	22.1	22.3	22.6	22.9	23.2	23.4	23.7	24.0	24.3	24.6	24.9	25.2	25.5	25.8	26.1	26.4	26.7	27.1	27.4	27.7	28.0	28.4	28.7	29.1	29.4	29.8	30.1	30.5	30.9	31.2	
	lard r		5% 10%			15					16										18									20					_	
	Stanc		1%	14.7		15.0		15.4		15.8		16.2		16.5		16.9		17.4		17.8		18.2		18.7		19.1		19.6		20.0		20.5		21.0		
		0.1%	0.25% 0.5%	14.7	14.9	15.0	15.2	15.4	15.6	15.8	16.0	16.2	16.4	16.5	16.7	16.9	17.2	17.4	17.6	17.8	18.0	18.2	18.4	18.7	18.9	19.1	19.3	19.6	19.8	20.0	20.3	20.5	20.8	21.0	21.3	
		2%	5% 10%	10								1							12							13									_	
			1%	10.0		10.2		10.5		10.7		11.0		11.3		11.5		11.8		12.1		12.4		12.7		13.0		13.3		13.7		14.0		14.3		
		0.1%	0.25%	10.0	10.1	10.2	10.4	10.5	10.6	10.7	10.9	11.0	11.1	11.3	11.4	11.5	11.7	11.8	12.0	12.1	12.3	12.4	12.6	12.7	12.9	13.0	13.2	13.3	13.5	13.7	13.8	14.0	14.2	14.3	14.5	
				_																																_

Practical capacitor model and specifications

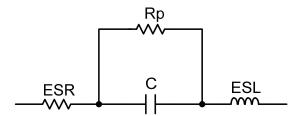
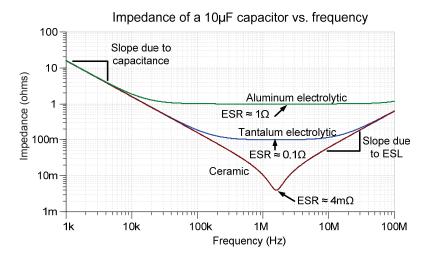


Figure 2: Model of a practical capacitor.

Table 9: Capacitor specifications

Parameter	Description
С	The nominal value of the capacitance.
	Table 11 lists standard capacitance values.
ESR	Equivalent series resistance.
	Ideally this is zero. Ceramic capacitors have the best ESR
	(typically in milliohms). Tantalum Electrolytic have ESR in the
	hundreds of milliohms and Aluminum Electrolytic have ESR in the
	ohms.
ESL	Equivalent series inductance.
	Ideally this is zero. ESL ranges from 100 pH to 10 nH.
Rp	Rp is a parallel leakage resistance (or insulation resistance).
	Ideally this is infinite. This can range from tens of megaohms for
	some electrolytic capacitors to tens of gigohms for ceramic.
Voltage rating	The maximum voltage that can be applied to the capacitor.
	Exceeding this rating damages the capacitor.
Voltage	The change in capacitance with applied voltage in ppm/V.
coefficient	A high-voltage coefficient can introduce distortion. COG capacitors
	have the lowest coefficient. The voltage coefficient is most
	important in applications that use capacitors in signal processing
	such as filtering.
Temperature	The change in capacitance with across temperature in ppm/°C.
coefficient	Ideally, the temperature coefficient is zero. The maximum
	specified drift generally ranges from 10 to 100ppm/°C depending
	on the resistor type.



Practical capacitors vs. frequency

Figure 3: Effect of ESR and ESL on capacitor frequency response

Table 10: Capacitor type overview

Capacitor type	Description
C0G/NP0	Use in signal path, filtering, low distortion, audio, and precision
(Type 1 ceramic)	Limited capacitance range: 0.1 pF to 0.47 µF
	Lowest temperature coefficient: ±30 ppm/°C
	Low-voltage coefficient
	Minimal piezoelectric effect
	Good tolerance: ±1% to ±10%
	Temperature range: –55°C to 125°C (150°C and higher)
	Voltage range may be limited for larger capacitance values
X7R	Use for decoupling and other applications where accuracy and
(Type 2 ceramic)	low distortion are not required
	X7R is an example of a type 2 ceramic capacitor
	See EIA capacitor tolerance table for details on other types
	Capacitance range: 10 pF to 47 µF
	Temperature coefficient: ±833 ppm/°C (±15% across temp range)
	Substantial voltage coefficient
	Tolerance: ±5% to -20%/+80%
	Temperature range: -55°C to 125°C
	Voltage range may be limited for larger capacitance values
Y5V	Use for decoupling and other applications where accuracy and
(Type 2 ceramic)	low distortion are not required
	Y5V is an example of a type 2 ceramic capacitor
	See EIA capacitor tolerance table for details on other types
	Temperature coefficient: -20%/+80% across temp range
	Temperature range: –30°C to 85°C
	Other characteristics are similar to X7R and other type 2 ceramic
Aluminum oxide	Use for bulk decoupling and other applications where large
electrolytic	capacitance is required
	Note that electrolytic capacitors are polarized and will be
	damaged, if a reverse polarity connection is made
	Capacitance range: 1 µF to 68,000 µF
	Temperature coefficient: ±30 ppm/°C
	Substantial voltage coefficient
	Tolerance: ±20%
	Temperature range: –55°C to 125°C (150°C and higher)
T	Higher ESR than other types
Tantalum	Capacitance range: 1 μ F to 150 μ F
electrolytic	Similar to aluminum oxide but smaller size
Polypropylene	Capacitance range: 100 pF to 10 μ F
film	Very low voltage coefficient (low distortion)
	Higher cost than other types
	Larger size per capacitance than other types
	Temperature coefficient: 2% across temp range
	Temperature range: –55°C to 100°C

Standard capacitance table											
1	1.1	1.2	1.3	1.5	1.6	1.8	2	2.2	2.4	2.7	3
3.3	3.6	3.9	4.3	4.7	5.1	5.6	6.2	6.8	7.5	8.2	9.1

Table 11: Standard capacitance table

СК 22	
Ţ	Ţ

Example

Translate the capacitor marking

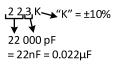


Figure 4: Capacitor marking code

Table 12: Ceramic capacitor tolerance markings

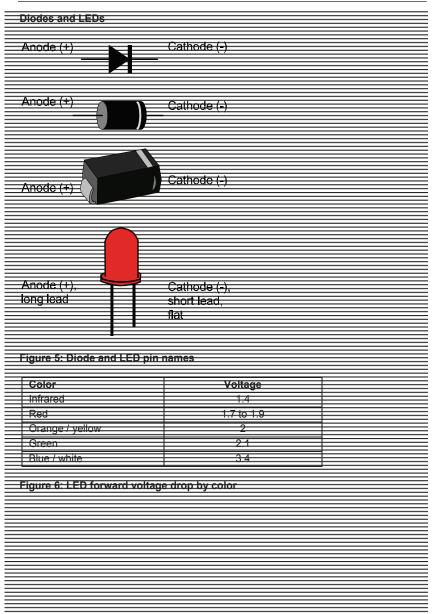
Code	Tolerance	Code	Tolerance
В	± 0.1 pF	J	± 5%
С	± 0.25 pF	К	± 10%
D	± 0.5 pF	М	± 20%
F	± 1%	Z	+ 80%, -20%
G	± 2%		

Table 13: EIA capacitor tolerance markings (Type 2 capacitors)

First letter	Low	Second number	Link town		Second	Max. capacitance
symbol	temp. limit	symbol	High temp. limit		letter symbol	change over temperature rating
Z	+10°C	2	+45°C	1	А	±1.0%
Y	–30°C	4	+65°C	1	В	±1.5%
Х	–55°C	5	+85°C	1	С	±2.2%
		6	+105°C	1	D	±3.3%
		7	+125°C	1	E	±4.7%
				1	F	±7.5%
				1	Р	±10.0%
				1	R	±15.0%
				1	S	±22.0%
					Т	±22% ~ 33%
				1	U	±22% ~ 56%
					V	±22% ~ 82%

Example

X7R: -55°C to +125°C, ±15.0%



• Capacitor equations (series, parallel, charge, energy)

- Inductor equations (series, parallel, energy)
- Capacitor charge and discharge
- RMS and mean voltage definition
- RMS for common signals
- Logarithm laws
- dB definitions
- · Pole and zero definition with examples

Analog



Capacitor equations

$$C_{t} = \frac{1}{\frac{1}{C_{1}} + \frac{1}{C_{2}} + \dots + \frac{1}{C_{N}}}$$
(1) Series capacitors

$$C_{t} = \frac{C_{1}C_{2}}{C_{1} + C_{2}}$$
(2) Two series capacitors

$$C_t = C_1 + C_2 + \dots + C_N$$
 (3) Parallel capacitors

Where

 C_t = equivalent total capacitance $C_1, C_2, C_3...C_N$ = component capacitors

$$Q = CV$$
 (4) Charge storage

Where

Q = charge in coulombs (C) C = capacitance in farads (F) I = current in amps (A) t = time in seconds (s)

$$i = C \frac{dv}{dt}$$
 (6) Instantaneous current through a capacitor

Where

i = instantaneous current through the capacitor C = capacitance in farads (F)

 $\frac{dv}{dt}$ = the instantaneous rate of voltage change

$$E = \frac{1}{2}CV^2$$
 (7) Energy stored in a capacitor

Where

20

E = energy stored in an capacitor in Joules (J)

V = voltage in volts

C = capacitance in farads (F)

4na/oo

Inductor equations

$$\begin{split} & L_t = L_1 + L_2 + \dots + L_N \\ & L_t = \frac{1}{\frac{1}{L_1} + \frac{1}{L_2} + \dots + \frac{1}{L_N}} \end{split} \tag{8} \quad \text{Series inductors} \\ & L_t = \frac{L_1 L_2}{L_1 + L_2} \end{aligned} \tag{9} \quad \text{Parallel inductors} \end{split}$$

Where

 $\label{eq:Lt} \begin{array}{l} L_t = equivalent \ total \ inductance \\ L_1, \ L_2, \ L_3 \dots L_N = component \ inductance \end{array}$

$$v = L \frac{di}{dt}$$
 (11) Instantaneous voltage across an inductor

Where

v = instantaneous voltage across the inductor L = inductance in Henries (H) $\frac{d}{dt}$ = the instantaneous rate of voltage change

$$E = \frac{1}{2}LI^2$$
 (12) Energy stored in an Inductor

Where

E = energy stored in an inductor in Joules (J) I = current in amps L = inductance in Henries (H)

Analog

Equation for charging a capacitor

$$V_{\rm C} = V_{\rm S} \left[1 - \mathrm{e}^{\left(\frac{-\mathrm{t}}{\tau}\right)} \right]$$

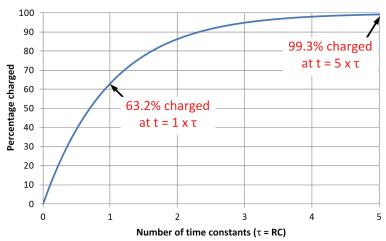
(13) General relationship

Where

 V_c = voltage across the capacitor at any instant in time (t) V_s = the source voltage charging the RC circuit t = time in seconds

 τ = RC, the time constant for charging and discharging capacitors

Graphing equation 13 produces the capacitor charging curve below. Note that the capacitor is 99.3% charged at five time constants. It is common practice to consider this *fully charged*.



Percentage charged vs. number of time constants

Figure 7: RC charge curve

Equation for discharging a capacitor

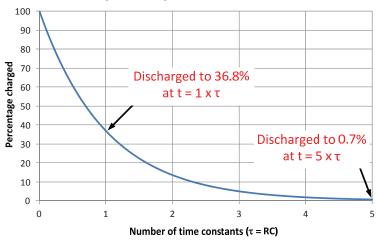
$$V_{C} = V_{i} \left[e^{\left(\frac{-t}{\tau}\right)} \right]$$

(14) General relationship

Where

 V_c = voltage across the capacitor at any instant in time (t) V_i = the initial voltage of the capacitor at t=0s t = time in seconds τ = RC, the time constant for charging and discharging capacitors

Graphing equation 14 produces the capacitor discharge curve below. Note that the capacitor is 0.7% charged at five time constants. It is common practice to consider this *fully discharged*.



Percentage discharged vs. number of time constants

Figure 8: RC discharge curve

Analog

RMS voltage

$$V_{RMS} = \sqrt{\frac{1}{(T_2 - T_1)} \int_{T_1}^{T_2} [V(t)]^2 dt}$$

(15) General relationship

Where $V(t) = \text{continuous function of time} \\ t = \text{time in seconds} \\ T_1 \leq t \leq T_2 = \text{the time interval that the function is defined over}$

Mean voltage

$$V_{MEAN} = \frac{1}{(T_2 - T_1)} \int_{T_1}^{T_2} V(t) dt$$

(16) General relationship

Where V(t) = continuous function of time t = time in seconds $T_1 \le t \le T_2$ = the time interval that the function is defined over

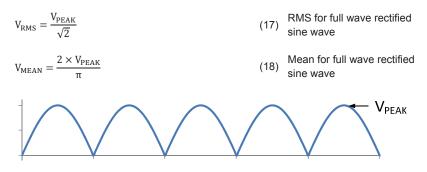


Figure 9: Full wave rectified sine wave



RMS voltage and mean voltage

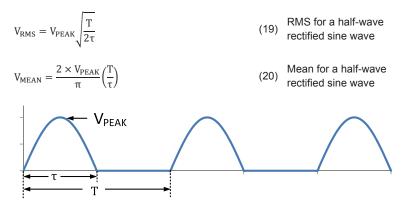


Figure 10: Half-wave rectified sine wave



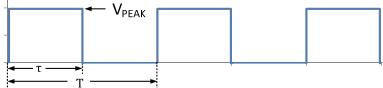
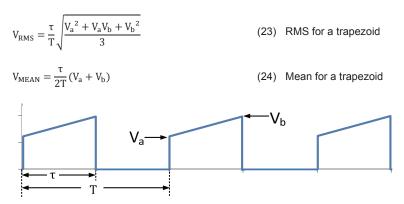


Figure 11: Square wave

Analog

RMS voltage and mean voltage





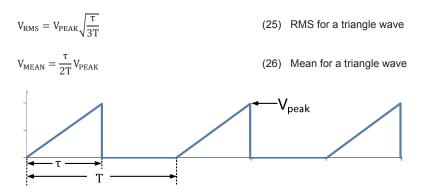


Figure 13: Triangle wave



Logarithmic mathematical definitions

$$\log\left(\frac{A}{B}\right) = \log(A) - \log(B)$$
$$\log(AB) = \log(A) + \log(B)$$
$$\log(A^{x}) = x \log(A)$$
$$\log_{b}(X) = \frac{\log_{a}(X)}{\log_{a}(b)}$$
$$\log_{2}(X) = \frac{\log_{10}(X)}{\log_{10}(2)}$$
$$\ln(X) = \log_{e}(X)$$
$$e = 2.718282$$

- (27) Log of dividend
- (28) Log of product
- (29) Log of exponent
- (30) Changing the base of log function
- (31) Example changing to log base 2
- (32) Natural log is log base e
- (33) Exponential function to 6 digits.

Alternative notations

$\exp(x) = e^x$	(34) Different notation for exponential function
$3.54E - 2 = 3.54 \times 10^{-2}$	Different notation for scientific (35) notation, sometimes confused with exponential function

dB definitions

Bode plot basics

The frequency response for the magnitude or gain plot is the change in voltage gain as frequency changes. This change is specified on a Bode plot, a plot of frequency versus voltage gain in dB (decibels). Bode plots are usually plotted as semi-log plots with frequency on the x-axis, log scale, and gain on the y-axis, linear scale. The other half of the frequency response is the phase shift versus frequency and is plotted as frequency versus degrees phase shift. Phase plots are usually plotted as semi-log plots with frequency on the x-axis, log scale, and phase shift on the y-axis, linear scale.

Definitions

Voltage gain (dB) = $20 \log \left(\frac{V_{OUT}}{V_{IN}} \right)$	(36) Voltage gain in decibels
Power gain (dB) = $10 \log \left(\frac{P_{OUT}}{P_{IN}}\right)$	(37) Power gain in decibels
Power gain (dBm) = $10 \log \left(\frac{P_{OUT}}{1 \text{ mW}}\right)$	(38) Power gain in decibel milliwatt

Table 14: Examples of common gain values and dB equivalent

A (V/V)	A (dB)
0.001	-60
0.01	-40
0.1	-20
1	0
10	20
100	40
1,000	60
10,000	80
100,000	100
1,000,000	120
10,000,000	140

Roll-off rate is the decrease in gain with frequency

Decade is a tenfold increase or decrease in frequency.(from 10 Hz to 100 Hz is one decade)

Octave is the doubling or halving of frequency (from 10 Hz to 20 Hz is one octave)



Figure 14 illustrates a method to graphically determine values on a logarithmic axis that are not directly on an axis grid line.

- 1. Given L = 1 cm; D = 2cm, measured with a ruler.
- 2. L/D = $log_{10}(f_P)$ 3. $f_P = 10^{(L/D)} = 10^{(1CM/2CM)} = 3.16$
- 4. Adjust for the decade range (for example, 31.6 Hz)

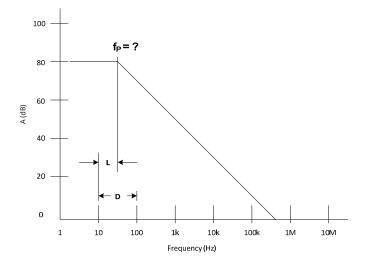


Figure 14: Finding values on logarithmic axis not directly on a grid line

Analog

Bode plots: Poles

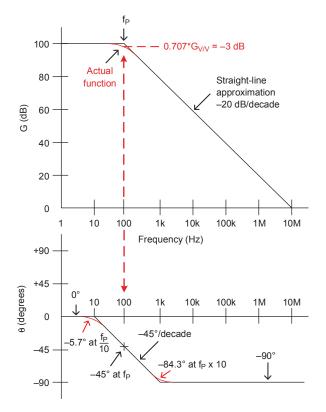


Figure 15: Pole gain and phase

 $\begin{array}{l} \mbox{Pole Location} = f_{\rm P} \mbox{ (cutoff freq)} \\ \mbox{Magnitude } (f < f_{\rm P}) = Gdc \mbox{ (for example, 100 dB)} \\ \mbox{Magnitude } (f = f_{\rm P}) = -3 \mbox{ dB} \\ \mbox{Magnitude } (f > f_{\rm P}) = -20 \mbox{ dB/decade} \\ \mbox{Phase } (f = f_{\rm P}) = -45^{\circ} \\ \mbox{Phase } (0.1 \mbox{ }_{f} < f < 10 \mbox{ }_{f}) = -45^{\circ} \mbox{/decade} \\ \mbox{Phase } (f > 10 \mbox{ }_{f}) = -90^{\circ} \\ \mbox{Phase } (f < 0.1 \mbox{ }_{f}) = 0^{\circ} \\ \end{array}$



Pole (equations)

$$G_{V} = \frac{V_{OUT}}{V_{IN}} = \frac{G_{DC}}{i\left(\frac{f}{f_{P}}\right) + 1}$$

$$G_V = \frac{V_{OUT}}{V_{IN}} = \frac{G_{DC}}{\sqrt{\left(\frac{f}{f_P}\right)^2 + 1}}$$

 $\theta = -\tan^{-1}\left(\frac{f}{f_{\rm p}}\right)$

$$G_{dB} = 20 \text{ Log}(G_V)$$

Where

 $\begin{array}{l} G_v = \mbox{voltage gain in V/V} \\ G_{dB} = \mbox{voltage gain in decibels} \\ G_{dc} = \mbox{the dc or low frequency voltage gain} \\ f = \mbox{frequency in Hz} \end{array}$

 f_P = frequency at which the pole occurs

 θ = phase shift of the signal from input to output

(39) As a complex number

- (41) Phase shift
- (42) Magnitude in dB

Analog

Bode plots (zeros)

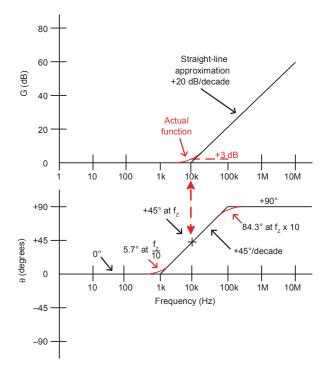


Figure 16: Zero gain and phase

Zero location = f_z Magnitude (f < f_z) = 0 dB Magnitude (f = f_z) = +3 dB Magnitude (f > f_z) = +20 dB/decade Phase (f = f_z) = +45° Phase (0.1 f_z < f < 10 f_z) = +45°/decade Phase (f > 10 f_z) = +90° Phase (f < 0.1 f_z) = 0°



Zero (equations)

$$G_{V} = \frac{V_{OUT}}{V_{IN}} = G_{DC} \left[i \left(\frac{f}{f_{Z}} \right) + 1 \right]$$

$$G_{V} = \frac{V_{OUT}}{V_{IN}} = G_{DC} \sqrt{\left(\frac{f}{f_{Z}}\right)^{2} + 1}$$

 $\theta = \tan^{-1} \left(\frac{f}{f_Z} \right)$

$$G_{dB} = 20 \text{ Log}(G_V)$$

Where

 $G_V = \text{voltage gain in V/V} \\ G_{dB} = \text{voltage gain in decibels} \\ G_{DC} = \text{the dc or low frequency voltage gain} \\ f = \text{frequency in Hz} \\ f_z = \text{frequency at which the zero occurs}$

 θ = phase shift of the signal from input to output

(43) As a complex number

(44) Magnitude

- (45) Phase shift
- (46) Magnitude in dB

Analog

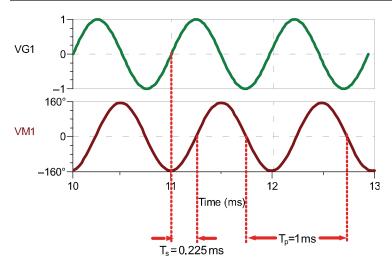


Figure 17: Time to phase shift

$$\Theta = \frac{T_S}{T_P} * 360^{\circ} \tag{47} \label{eq:eq:eq:expansion} \label{eq:expansion}$$

Where

 T_s = time shift from input to output signal

 T_P = period of signal

 θ = phase shift of the signal from input to output

Example

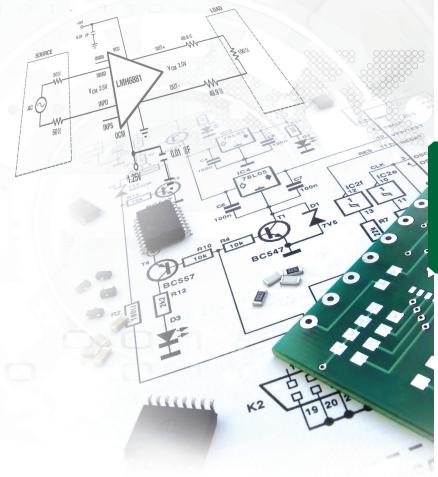
Calculate the phase shift in degrees for Figure 17.

Answer

$$\theta = \frac{T_{s}}{T_{P}} * 360^{\circ} = \left(\frac{0.225 \text{ ms}}{1 \text{ ms}}\right) * 360^{\circ} = 81^{\circ}$$

Basic op amp configurations

- Op amp bandwidth
- Full power bandwidth
- Small signal step response
- Noise equations
- Stability equations
- Stability open loop SPICE analysis



Amplifier

Amplifier



Basic op amp configurations

$$G_{CL} = 1$$

(48) Gain for buffer configuration

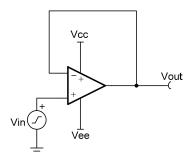
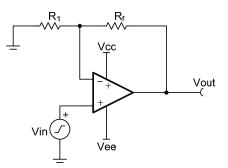
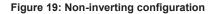


Figure 18: Buffer configuration

$$G_{CL} = \frac{R_f}{R_1} + 1$$

(49) Gain for non-inverting configuration







Basic op amp configurations (cont.)

$$G_{CL} = -\frac{R_f}{R_1}$$
(50)

Gain for inverting configuration

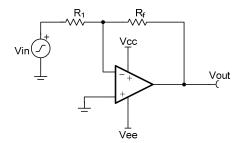


Figure 20: Inverting configuration

$$V_{OUT} = -R_f(\frac{V_1}{R_1} + \frac{V_2}{R_2} + \dots + \frac{V_N}{R_N})$$

$$V_{OUT} = -\frac{R_f}{R_1}(V_1 + V_2 + \dots + V_N)$$

(52) Transfer function for inverting (52) summing amplifier, assuming $R_1 = R_2 = ... = R_N$

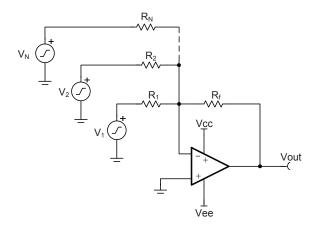


Figure 21: Inverting summing configuration

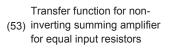
Amplifier

Basic op amp configurations (cont.)

$$V_{OUT} = \left(\frac{R_{f}}{R_{in}} + 1\right) \left[\frac{V_{1}}{N} + \frac{V_{2}}{N} + \dots + \frac{V_{N}}{N}\right]$$

Where

 $R_1 = R_2 = ... = R_N$ N = number of input resistors



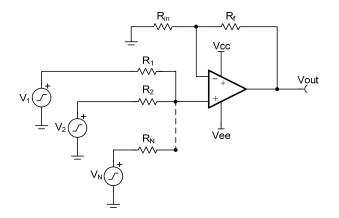


Figure 22: Non-inverting summing configuration

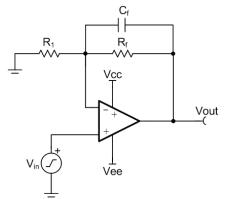


Simple non-inverting amp with C_f filter

$$G_{\rm LF} = \frac{R_{\rm f}}{R_{\rm 1}} + 1$$
(54)

 $G_{\rm HF} = 1 \tag{55}$

$$f_{\rm C} = \frac{1}{2\pi R_{\rm f} C_{\rm f}} \tag{56}$$



- Gain for non-inverting configuration for f < $f_{\rm c}$
- Gain for non-inverting configuration for f >> $f_{\rm c}$

Cut off frequency for non-inverting configuration

Figure 23: Non-inverting amplifier with C_f filter

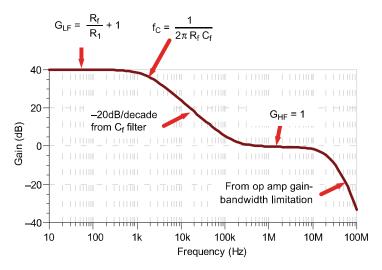


Figure 24: Frequency response for non-inverting op amp with C_f filter

Simple inverting amp with C_f filter

$$G_{LF} = -\frac{R_f}{R_c}$$
 (57) Gain for inverting configuration
for f < f_c

(58) Gain for inverting configuration for
$$f >> f_c$$

$$f_C = \frac{1}{2\pi R_f C_f}$$

 $G_{HF} = 1$

(59) Cutoff frequency for inverting configuration

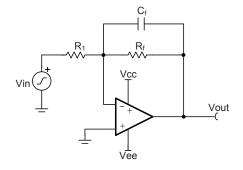


Figure 25: Inverting amplifier with C_f filter

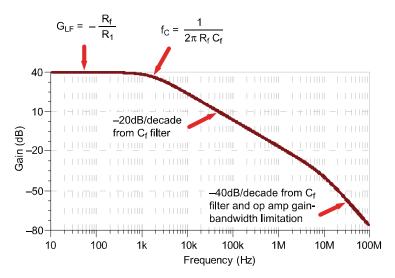


Figure 26: Frequency response for inverting op amp with C_f filter



Op amp bandwidth

 $GBW = Gain \times BW$ (60) Gain bandwidth product defined

Where

GBW = gain bandwidth product, listed in op amp data sheet specification table Gain = closed loop gain, set by op amp gain configuration BW = the bandwidth limitation of the amplifier

Example

Determine bandwidth using equation 60

Gain = 100	(from amplifier configuration)
GBW = 22MHz	(from data sheet)
$BW = \frac{GBW}{Gain} = \frac{22MHz}{100} = 220kHz$	

Note that the same result can be graphically determined using the $A_{\mbox{\scriptsize OL}}$ curve as shown below.

Open-loop gain and phase vs. frequency

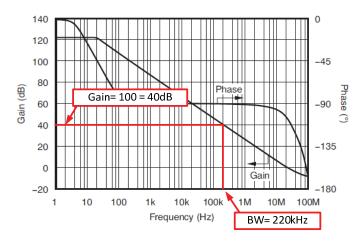


Figure 27: Using A_{OL} to find closed-loop bandwidth

Amplifier

Full power bandwidth

$$V_{\rm P} = \frac{\rm SR}{2\pi f}$$

(61) Maximum output without slew-rate induced distortion

Where

 V_P = maximum peak output voltage before slew induced distortion occurs SR = slew rate f = frequency of applied signal

Maximum output voltage vs. frequency

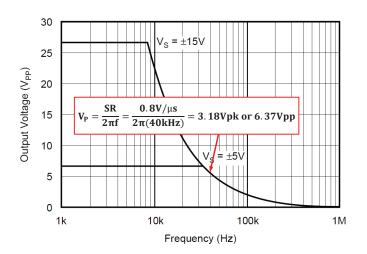


Figure 28: Maximum output without slew-rate induced distortion

Notice that the above figure is graphed using equation 61 for the OPA188. The example calculation shows the peak voltage for the OPA277 at 40kHz. This can be determined graphically or with the equation.

Example

$$V_{\rm P} = \frac{SR}{2\pi f} = \frac{0.8V/\mu s}{2\pi (40 \text{kHz})} = 3.18 \text{Vpk or } 6.37 \text{Vpp}$$

Small signal step response

$$\tau_{\rm R} = \frac{0.35}{f_{\rm C}}$$

(62) Rise time for a small signal step

Where

 τ_R = the rise time of a small signal step response

 f_{C} = the closed-loop bandwidth of the op amp circuit

Small signal step response waveform

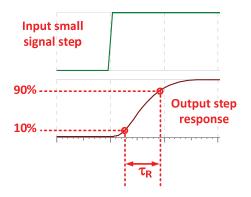


Figure 29: Small signal step response

Amplifier

Op amp noise model

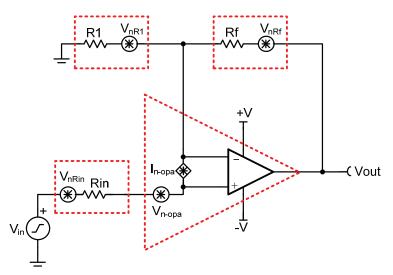


Figure 30: Op amp noise model

Op amp intrinsic noise includes:

- Noise caused by op amp (current noise + voltage noise)
- Resistor noise

Noise bandwidth calculation

$$BW_N = K_N f_C$$
 (63) Noise bandwidth

Where

 BW_N = noise bandwidth of the system K_N = the brick wall correction factor for different filter order f_C = -3 dB bandwidth of the system

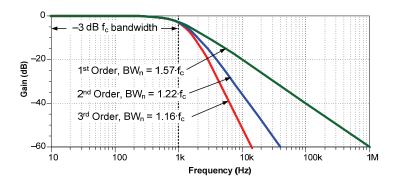


Figure 31: Op amp bandwidth for three different filters orders

Number of poles	K _N brick wall correction factor
1	1.57
2	1.22
3	1.13
4	1.12

Table 15: Brick wall correction factors for noise bandwidth

Broadband total noise calculation

 $E_N = e_{BB} \sqrt{BW_N}$

(64) Total rms noise from broadband

Where

 E_N = total rms noise from broadband noise e_{BB} = broadband noise spectral density (nV/rtHz) BW_N = noise bandwidth (Hz)

Amplifier

1/f total noise calculation

 $E_{N_NORMAL} = e_{BF}\sqrt{f_0}$ (65) Normalized 1/f noise at 1 Hz

Where

$$\begin{split} & E_{N_NORMAL} = 1/f \text{ noise normalized to 1 Hz} \\ & e_{BF} = \text{ noise spectral density measured in the 1/f region} \\ & f_{O} = \text{the frequency that the 1/f noise } e_{BF} \text{ is measured at} \end{split}$$

$$E_{N_{LICKER}} = E_{N_{NORMAL}} \ln \left(\frac{f_{H}}{f_{L}} \right)$$

(66) 1/f total noise calculation

Where

$$\begin{split} & E_{N_FLICKER} = \text{total rms noise from flicker} \\ & E_{N_NORMAL} = 1/\text{f noise normalized to 1 Hz} \\ & f_{H} = \text{upper cutoff frequency or noise bandwidth} \\ & f_{L} = \text{lower cutoff frequency, normally set to 0.1 Hz} \end{split}$$

Table 16: Peak-to-peak conversion

Number of standard deviations	Percent chance reading is in range
2σ (same as ±1σ)	68.3%
3σ (same as ±1.5σ)	86.6%
4σ (same as ±2σ)	95.4%
5σ (same as ±2.5σ)	98.8%
6σ (same as ±3σ)	99.7%
6.6σ (same as ±3.3σ)	99.9%

Thermal noise calculation

$$E_{N_R} = \sqrt{4 \text{ kTR}\Delta f}$$

(67) Total rms thermal noise

Where

 $E_{N_{L}R}$ = total rms noise from resistance, also called thermal noise k = Boltzmann's constant 1.38 x 10⁻²³ J/K T = temperature in Kelvin Δf = noise bandwidth in Hz

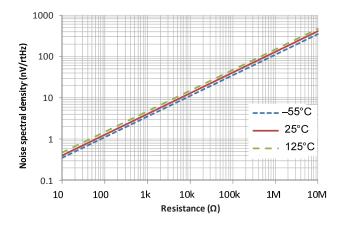


Figure 32: Noise spectral density vs. resistance

Amplifier

Ac response versus frequency

Figure 33 illustrates a bode plot with four different examples of ac peaking.

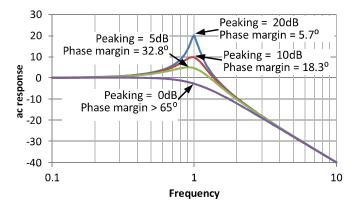


Figure 33: Stability – ac peaking relationship example

Phase margin versus ac peaking

This graph illustrates the phase margin for any given level of ac peaking. Note that 45° of phase margin or greater is required for stable operation.

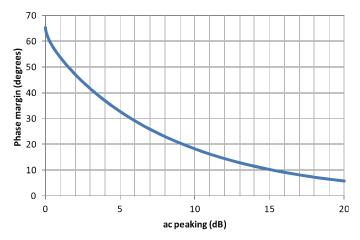


Figure 34: Stability – phase margin vs. peaking for a two-pole system



Transient overshoot

Figure 35 illustrates a transient response with two different examples of percentage overshoot.

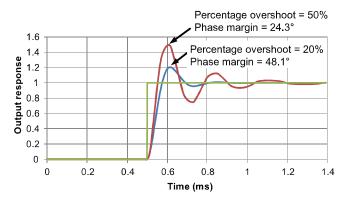
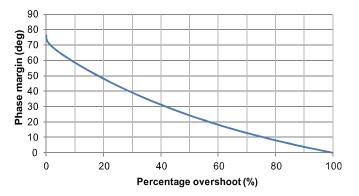
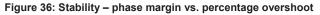


Figure 35: Stability – transient overshoot example

Phase margin versus percentage overshoot

This graph illustrates the phase margin for any given level of transient overshoot. Note that 45° of phase margin or greater is required for stable operation.





Note: The curves assume a two-pole system.

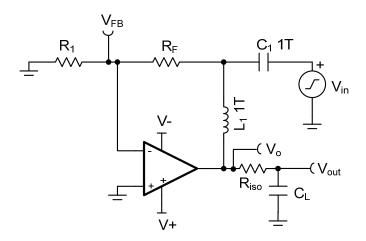


Figure 37: Common spice test circuit used for stability

$A_{OL_LOADED} = \frac{V_O}{V_{FB}}$	(68)	Loaded open-loop gain
$\beta = V_{FB}$	(69)	Feedback factor
$\frac{1}{\beta} = \frac{1}{V_{FB}}$	(70)	Closed-loop noise gain
$A_{OL_LOADED} \times \beta = V_O$	(71)	Loop gain

Where

 $V_{\rm O}$ = the voltage at the output of the op amp.

 V_{OUT} = the voltage output delivered to the load, which may be important to the application but is not considered in stability analysis.

V_{FB} = feedback voltage

 $R_{\rm F}$, R_1 , $R_{\rm ISO}$ and $C_{\rm L}$ = the op amp feedback network and load. Other op amp topologies will have different feedback networks; however, the test circuit will be the same for most cases. Figure 38 shows the exception to the rule (multiple feedback). C_1 and L_1 are components that facilitate SPICE analysis. They are large (1TF, 1TH) to make the circuit closed-loop for dc, but open loop for ac frequencies. SPICE requires closed-loop operation at dc for convergence.



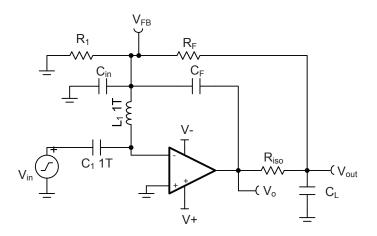


Figure 38: Alternative (multiple feedback) SPICE test circuit used for stability

(72)

Loaded open loop gain

gain

Feedback factor

 $A_{OL_LOADED} = V_0$

$$\beta = \frac{V_{FB}}{V_0}$$
(73)

$$\frac{1}{\beta} = \frac{V_{O}}{V_{FB}}$$
(74) Closed-loop noise
$$A_{OL \ LOADED} \times \beta = V_{FB}$$
(75) Loop gain

Where

 $V_{\rm O}$ = the voltage at the output of the op amp.

 V_{OUT} = the voltage output delivered to the load. This may be important to the application but is not considered in stability analysis.

V_{FB} = feedback voltage

 R_F , R_1 , R_{ISO} and C_F = the op amp feedback network. Because there are two paths for feedback, the loop is broken at the input.

 C_1 and L_1 are components that facilitate SPICE analysis. They are large (1TF, 1TH) to make the circuit closed loop for dc, but open loop for ac frequencies. SPICE requires closed-loop operation at dc for convergence.

 C_{IN} = the equivalent input capacitance taken from the op amp datasheet. This capacitance normally does not need to be added because the model includes it. However, when using this simulation method the capacitance is isolated by the 1TH inductor.

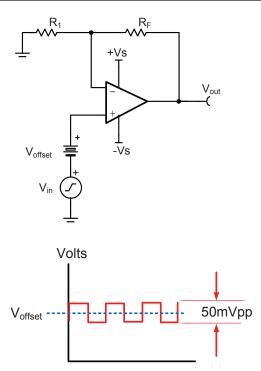


Figure 39: Transient real world stability test

Test tips

- Choose test frequency << f_{cl}
- Small signal (Vpp ≤ 50 mV) ac output square wave (for example, 1 kHz)
- Adjust V_{in} amplitude to yield output ≤ 50 mVpp
- Worst cases is usually when $V_{offset} = 0$ (Largest Ro, for $I_{out} = 0A$).
- User V_{offset} as desired to check all output operating points for stability
- Set scope = ac couple and expand vertical scope scale to look for amount of overshoot, undershoot, and ringing on V_{out}
- Use 1x attenuation scope probe on V_{out} for best resolution

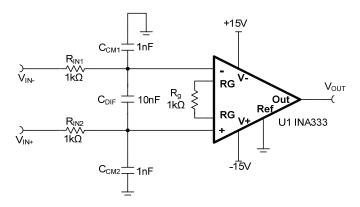


Figure 40: Input filter for instrumentation amplifier

Select
$$C_{DIF} \ge 10C_{CM1}$$

 $R_{IN1} = R_{IN2}$
 $C_{CM1} = C_{CM2}$
 $f_{CM} = \frac{1}{2\pi R_{IN1}C_{CM1}}$

$$f_{DIF} = \frac{1}{2\pi (2R_{IN1})(C_{DIF} + \frac{1}{2}C_{CM1})}$$

Where f_{DIF} = differential cutoff frequency f_{CM} = common-mode cutoff frequency R_{IN} = input resistance C_{CM} = common-mode filter capacitance C_{DIF} = differential filter capacitance

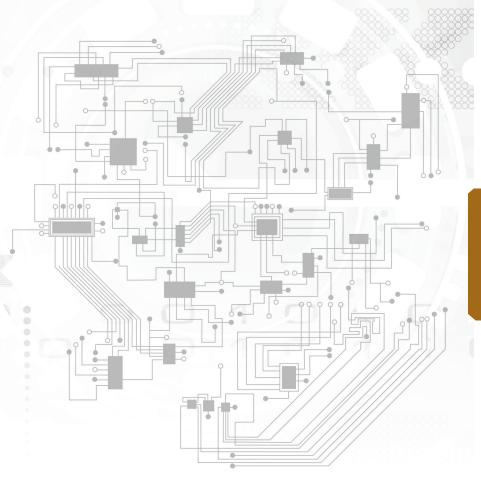
Note: Selecting $C_{\text{DIF}} \ge 10 C_{\text{CM}}$ sets the differential mode cutoff frequency 10 times lower than the common-mode cutoff frequency. This prevents common-mode noise from being converted into differential noise due to component tolerances.

- (76) Differential filter is sized 10
- times the common-mode filter
- (77) Input resistors must be equal
- (78) Common-mode capacitors must be equal
- (79) Differential filter cutoff
- (80) Common-mode filter cutoff



lotes	

- PCB trace resistance for 1oz and 2oz Cu
- Conductor spacing in a PCB for safe operation
- · Current carrying capacity of copper conductors
- Package types and dimensions
- PCB trace capacitance and inductance
- PCB via capacitance and inductance
- Common coaxial cable specifications
- Coaxial cable equations
- Resistance per length for wire types
- Maximum current for wire types



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Voltage between	Minimum spacing						
conductors (dc or ac		Bare t	oard			Assembly	
peaks)	B1	B2	B3	B4	A5	A6	A7
0-15	0.05 mm	0.1 mm	0.1 mm	0.05 mm	0.13 mm	0.13 mm	0.13 mm
	[0.00197 in]	[0.0039 in]	[0 0039 in]	[0.00197 in]	[0.00512 in]	[0.00512 in]	[0.00512 in]
16-30	0.05 mm	0.1 mm	0.1 mm	0.05 mm	0.13 mm	0.25 mm	0.13 mm
	[0.00197 in]	[0.0039 in]	[0.0039 in]	[0.00197 in]	[0.00512 in]	[0.00984 in]	[0.00512 in]
31-50	0.1 mm	0.6 mm	0.6 mm	0.13 mm	0.13 mm	0.4 mm	0.13 mm
	[0.0039 in]	[0.024 in]	[0.024 in]	[0.00512 in]	[0.00512 in]	[0.016 in]	[0.00512 in]
51-100	0.1 mm	0.6 mm	1.5 mm	0.13 mm	0.13 mm	0.5 mm	0.13 mm
	[0.0039 in]	[0.024 in]	[0.0591 in]	[0.00512 in]	[0.00512 in]	[0.020 in]	[0.00512 in]
101-150	0.2 mm	0.6 mm	3.2 mm	0.4 mm	0.4 mm	0.8 mm	0.4 mm
	[0.0079 in]	[0.024 in]	[0.126 in]	[0.016 in]	[0.016 in]	[0.031 in]	[0.016 in]
151-170	0.2 mm	1.25 mm	3.2 mm	0.4 mm	0.4 mm	0.8 mm	0.4 mm
	[0.0079 in]	[0.0492 in]	[0.126 in]	[0.016 in]	[0.016 in]	[0.031 in]	[0.016 in]
171-250	0.2 mm	1.25 mm	6.4 mm	0.4 mm	0.4 mm	0.8 mm	0.4 mm
	[0.0079 in]	[0.0492 in]	[0.252 in]	[0.016 in]	[0.016 in]	[0.031 in]	[0.016 in]
251-300	0.2 mm [0.0079 in]	1.25 mm [0.0492 in]		0.4 mm [0.016 in]	0.4 mm [0.016 in]	0.8 mm [0.031 in]	0.8 mm [0.031 in]
301-500	0.25 mm	2.5 mm	12.5 mm	0.8 mm	0.8 mm	1.5 mm	0.8 mm
	[0.00984 in]	[0.0984 in]	[0.492 in]	[0.031 in]	[0.031 in]	[0.0591 in]	[0.031 in]

B1 Internal conductors

B2 External conductors uncoated sea level to 3050 m

B3 External conductors uncoated above 3050 m

B4 External conductors coated with permanent polymer coating (any elevation)

A5 External conductors with conformal coating over assembly (any elevation)

A6 External component lead/termination, uncoated, sea level to 3050 m

A7 External component lead termination, with conformal coating (any elevation)

Extracted with permission from IPC-2221B, Table 6-1.

For additional information, the entire specification can be downloaded at www.ipc.org

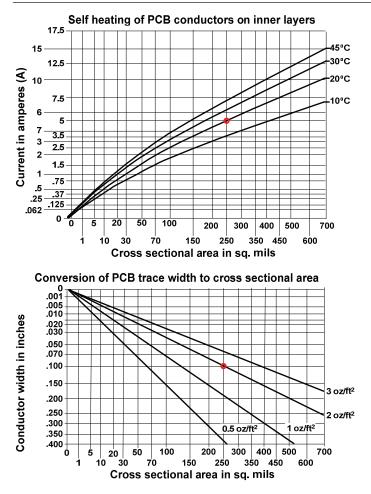


Figure 41: Self heating of PCB traces on inside layer

Example

Find the current that will cause a 20°C temperature rise in a PCB trace that is 0.1 inch wide and uses 2 oz/ ft^2 copper. (Assume traces on outside of PCB.)

Answer

First translate 0.1 inch to 250 sq. mils. using bottom chart. Next find the current associated with 10°C and 250 sq. mils. using top chart (Answer = 5A).

Extracted with permission from IPC-2152, Figure 5-1. For additional information the entire specification can be downloaded at <u>www.ipc.org</u>

PCB trace resistance for 1 oz Cu

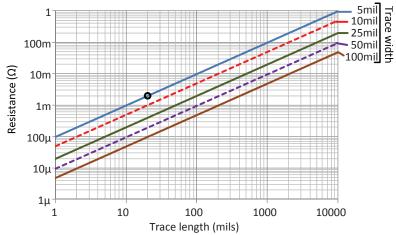


Figure 42: PCB trace resistance vs. length and width for 1 oz-Cu, 25°C

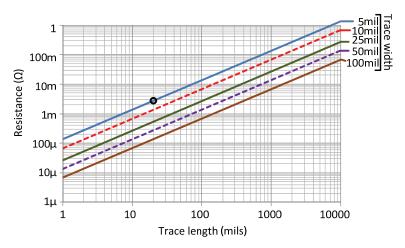


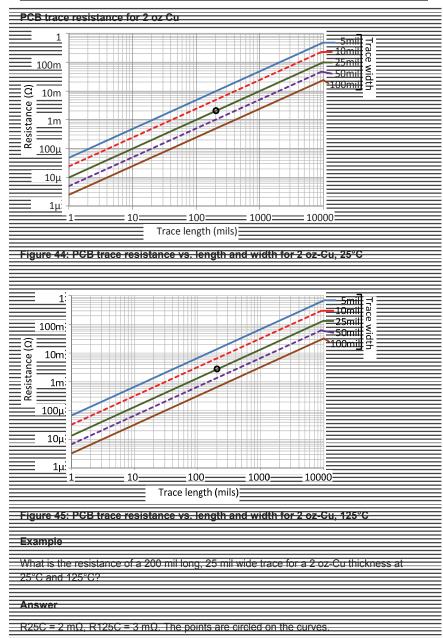
Figure 43: PCB trace resistance vs. length and width for 1 oz-Cu, 125°C

Example

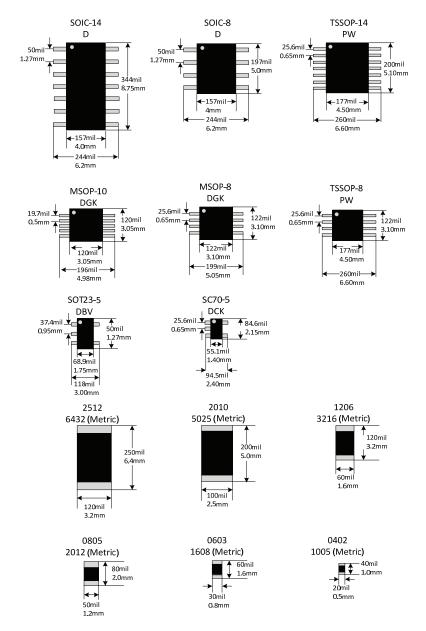
What is the resistance of a 20 mil long, 5 mil wide trace for a 1 oz-Cu thickness at 25° C and 125° C?

Answer

R25C = 2 m Ω , R125C = 3 m Ω . The points are circled on the curves.



Common package type and dimensions



PCB parallel plate capacitance

$$C(pF) = \frac{2.249 * 10^{-4} * \varepsilon_r * l * w}{h}$$

Capacitance for parallel copper planes

Where

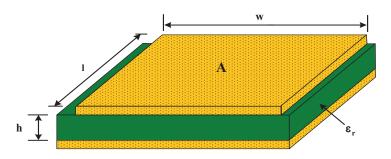
$$\begin{split} \epsilon_r &= \text{PCB dielectric constant } (\epsilon_r \approx 4.2 \text{ for FR-4}) \\ \text{I} &= \text{common length of copper planes (mils)} \\ \text{w} &= \text{common width of copper planes (mils)} \\ \text{h} &= \text{separation between copper planes (mils)} \end{split}$$

Example

 $\varepsilon_r = 4.2$ l = 400 mils w = 400 mils h = 63 mils

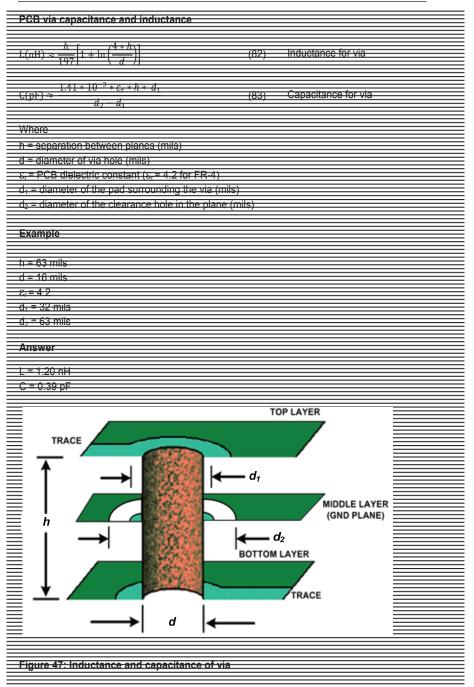
Answer

C = 2.4 pF



(81)

Figure 46: PCB parallel plate capacitance



Adjacent copper trace capacitance

$$C(\mathrm{pF}) \approx \frac{2.249 * 10^{-4} * l * t}{d}$$
 (58) Same layer

$$C(\text{pF}) \approx \frac{2.249 * 10^{-4} * \varepsilon_{\text{r}} * l * w}{h}$$
 (59) Different layers

Where

 $\label{eq:linear_line$

Example

 $\label{eq:last} \begin{array}{l} \mathsf{I} = 100 \text{ mils} \\ \mathsf{t} = 1.37 \text{ mils} \ (1 \text{ oz. copper}) \\ \mathsf{d} = 10 \text{ mils} \\ \epsilon_r = 4.2 \\ \mathsf{w} = 25 \text{ mils} \\ \mathsf{h} = 63 \text{ mils} \end{array}$

Answer

C (same layer) = 0.003 pF C (different layers) = 0.037 pF

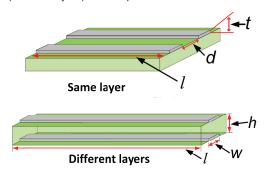


Figure 48: Capacitance for adjacent copper traces

Table 18: Coaxial cable information

Type	Zo	Capacitance / length (pF/feet)	Outside diameter (inches)	dB attenuation /100 ft at 750 MHz	Dielectric type	Application
RG-58	53.5 Ω	28.8	0.195	13.1	PE	Test equipment and RF power to a few hundred watts, and a couple hundred MHz
RG-8	52 Ω	29.6	0.405	5.96	PE	
RG-214/U	50 Ω	30.8	0.425	6.7	PE	RF power to a few kW, up to several hundred MHz
9914	50 Ω	26.0	0.405	4.0	PE	
RG-6	75 Ω	20	0.270	5.6	PF	Video and CATV applications. RF to a few hundred watts, up to a few hundred MHz,
RG-59/U	73 Ω	29	0.242	9.7	PE	sometimes to higher frequencies if losses can be tolerated
RG-11/U	75 Ω	17	0.412	3.65	PE	RF power to a few kW, up to several hundred MHz
RG-62/U	93 Ω	13.5	0.242	7.1	ASP	Used in some test equipment and 100 Ω video applications
RG-174	50 Ω	31	0.100	23.5	PE	Miniature coax used primarily for test equipment
RG-178/U	50 Ω	29	0.071	42.7	ST	interconnection. Usually short runs due to higher loss.

Coaxial cable equations

$$\frac{C}{l} = \frac{2\pi\epsilon}{\ln\left(\frac{D}{d}\right)}$$
(84) Capacitance per length

$$\frac{L}{l} = \frac{\mu}{2\pi} \ln\left(\frac{D}{d}\right)$$
(85) Inductance per length
$$z = \sqrt{\frac{L}{L}} = \frac{1}{2\pi} \sqrt{\frac{\mu}{L}}$$
(86) Characteristic impedance

$$Z_o = \sqrt{\frac{L}{C}} = \frac{1}{2\pi} \sqrt{\frac{\mu}{\epsilon}}$$
 (86) Characteristic imperiation (86)

Where

L = inductance in henries (H) C = capacitance in farads (F) Z = impedance in ohms (Ω) d = diameter of inner conductor D = inside diameter of shield, or diameter of dielectric insulator ε = dielectric constant of insulator ($\varepsilon = \varepsilon_r \varepsilon_o$)

 μ = magnetic permeability (μ = μ _r μ _o)

I = length of the cable

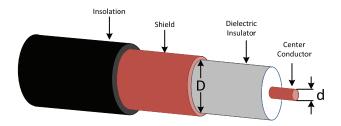


Figure 49: Coaxial cable cutaway

AWG	Stds	Outside	diameter	Area	a	dc resist	dc resistance	
		in	mm	circular mils	mm²	Ω / 1000 ft	Ω/km	
36	Solid	0.005	0.127	25	0.013	445	1460	
36	7/44	0.006	0.152	28	0.014	371	1271	
34	Solid	0.0063	0.160	39.7	0.020	280	918	
34	7/42	0.0075	0.192	43.8	0.022	237	777	
32	Solid	0.008	0.203	67.3	0.032	174	571	
32	7/40	0.008	0.203	67.3	0.034	164	538	
30	Solid	0.010	0.254	100	0.051	113	365	
30	7/38	0.012	0.305	112	0.057	103	339	
28	Solid	0.013	0.330	159	0.080	70.8	232	
28	7/36	0.015	0.381	175	0.090	64.9	213	
26	Solid	0.016	0.409	256	0.128	43.6	143	
26	10/36	0.021	0.533	250	0.128	41.5	137	
24	Solid	0.020	0.511	404	0.205	27.3	89.4	
24	7/32	0.024	0.610	448	0.229	23.3	76.4	
22	Solid	0.025	0.643	640	0.324	16.8	55.3	
22	7/30	0.030	0.762	700	0.357	14.7	48.4	
20	Solid	0.032	0.813	1020	0.519	10.5	34.6	
20	7/28	0.038	0.965	1111	0.562	10.3	33.8	
18	Solid	0.040	1.020	1620	0.823	6.6	21.8	
18	7/26	0.048	1.219	1770	0.902	5.9	19.2	
16	Solid	0.051	1.290	2580	1.310	4.2	13.7	
16	7/24	0.060	1.524	2828	1.442	3.7	12.0	
14	Solid	0.064	1.630	4110	2.080	2.6	8.6	
14	7/22	0.073	1.854	4480	2.285	2.3	7.6	

Table 19: Resistance per length for different wire types (AWG)

Wire gauge	Polyethylene Neoprene Polyvinylchloride (semi-ridged) at 80°C	Polypropylene Polyethylene (high density) at 90°C	Polyvinylchloride Nylon at 105°C	Kynar Polyethylene Thermoplastic at 125°C	Kapton Teflon Silicon at 200°C
AWG	I _{max} (A)	I _{max} (A)	I _{max} (A)	I _{max} (A)	I _{max} (A)
30	2	3	3	3	4
28	3	4	4	5	6
26	4	5	5	6	7
24	6	7	7	8	10
22	8	9	10	11	13
20	10	12	13	14	17
18	15	17	18	20	24
16	19	22	24	26	32
14	27	30	33	40	45
12	36	40	45	50	55
10	47	55	58	70	75
Note: \	Nire is in free	air at 25°C			

Table 20: Maximum current vs. AWG

Example

What is the maximum current that can be applied to a 30 gauge Teflon wire in a room temperature environment? What will the self-heating be?

Answer

I_{max} = 4A Wire temperature = 200°C

Notes	

Sensor

10:15

Menu

Humidity 49%

FAN

MODE

TIMER

- Thermistor
- Resistive temperature detector (RTD)
- Diode temperature characteristics
- Thermocouple (J and K)



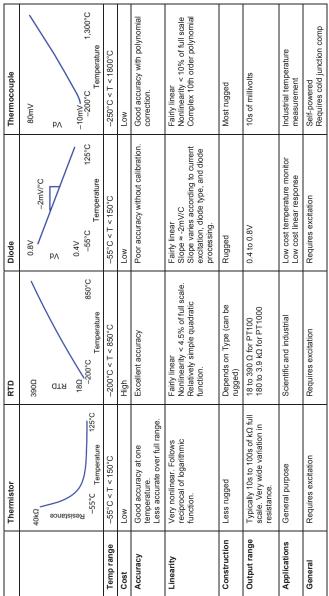


Table 21: Temperature sensor overview

Sensor



Thermistor: Resistance to temperature, Steinhart-Hart equation

$$\frac{1}{T} = a + b \ln(R) + c \left(\ln(R) \right)^3$$

(87)

Convert resistance to

temperature for a thermistor

Where

T = temperature in Kelvin a, b, c = Steinhart-Hart equation constants R = resistance in ohms

Thermistor: Temperature to resistance, Steinhart-Hart equation

$$R = \exp\left(x - \frac{y}{2}\right)^{\frac{1}{3}} - \exp\left(x - \frac{y}{2}\right)^{\frac{1}{3}}$$
(88) Convert temperature to resistance for a thermistor

$$y = \frac{a - \frac{1}{T}}{c}$$
 (89) Factor used in Equation 88

$$x = \sqrt{\left(\frac{b}{3 c}\right)^3 + \frac{y^2}{4}}$$
 (90) Factor used in Equation 88

Where

R = resistance in ohms

T = temperature in Kelvin

a, b, c = Steinhart-Hart equation constants

x, y = Steinhart-Hart factors used in temperature to resistance equation

RTD equation temperature to resistance

$$R_{rtd} = R_o [1 + A_o T + B_o T^2 + C_o (T - 100)T^3]$$

$$(91) \begin{array}{c} \text{RID resistance} \\ \text{T<0°C} \end{array}$$

$$R_{rtd} = R_o [1 + A_o T + B_o T^2]$$

$$(92) \begin{array}{c} \text{RTD resistance} \\ \text{T>0°C} \end{array}$$

for

for

Where

 $\begin{array}{l} R_{rtd} = resistance \ of \ RTD \ over \ temperature \ range \ of \ (-200^{\circ}C < T < 850^{\circ}C) \\ R_{o} = 100 \ \Omega \ for \ PT-100, \ 1000 \ \Omega \ for \ PT-1000 \\ A_{O}, \ B_{O}, \ C_{O} = Callendar-Van \ Dusen \ coefficients \\ T = temperature \ in \ degrees \ Celsius \ (^{\circ}C) \end{array}$

RTD equation resistance to temperature (T>0°C)

$$T = \frac{-A_0 + \sqrt{A_0^2 + 4B_0 \left(1 - \frac{R_{RTD}}{R_0}\right)}}{2B_0}$$
(93) RTD resistance for T>0°C

Where

 R_{RTD} = resistance of RTD over temperature range of (–200°C < T < 850°C) R_{o} = 100 Ω

A₀, B₀, C₀ = Callendar-Van Dusen coefficients

T = temperature in degrees Celsius (°C)

Table 22: Callendar-Van Dusen coefficients for different RTD standards

	IEC-751 DIN 43760 BS 1904 ASTM-E1137 EN-60751	JISC 1604	US Industrial Standard D-100 American	US Industrial Standard American	ITS-90
A0	+3.9083E-3	+3.9739E-3	+3.9787E-3	+3.9692E-3	+3.9888E-3
B0	-5.775E-7	-5.870E-7	-5.8686E-7	-5.8495E-7	-5.915E-7
C0	-4.183E-12	-4.4E-12	-4.167E-12	-4.233E-12	-3.85E-12

Example

What is the temperature given an ITS-90 PT100 resistance of 120 Ω ?

Answer

$$T = \frac{-(3.9888 \cdot 10^{-3}) + \sqrt{(3.9888 \cdot 10^{-3})^2 + 4(-5.915 \cdot 10^{-7})\left(1 - \frac{120}{100}\right)}}{2(-5.915 \cdot 10^{-7})} = 50.5^{\circ}C$$



RTD equation resistance to temperature (T<0°C)

$$T = \sum_{i=0}^{n} \alpha_i \left(R_{rtd} \right)^i$$

(94)

RTD resistance for T<0°C

Where

T = temperature in degrees Celsius (°C)

 R_{RTD} = resistance of RTD over temperature range of (T<0°C)

 α_l = polynomial coefficients for converting RTD resistance to temperature for T<0°C

Table 23: Coefficients for 5th order RTD resistance to temperature

	IEC-751 DIN 43760 BS 1904 ASTM-E1137 EN-60751	JISC 1604	US Industrial Standard D-100 American	US Industrial Standard American	ITS-90
α0	-2.4202E+02	-2.3820E+02	-2.3818E+02	-2.3864E+02	-2.3791E+02
α1	2.2228E+00	2.1898E+00	2.1956E+00	2.1973E+00	2.2011E+00
α2	2.5857E-03	2.5226E-03	2.4413E-03	2.4802E-03	2.3223E-03
α3	-4.8266E-06	-4.7825E-06	-4.7517E-06	-4.7791E-06	-4.6280E-06
α4	-2.8152E-08	-2.7009E-08	-2.3831E-08	-2.5157E-08	-1.9702E-08
α5	1.5224E-10	1.4719E-10	1.3492E-10	1.4020E-10	1.1831E-10

Example

Find the temperature given an ITS-90 PT100 resistance of 60 Ω .

Answer

$$\begin{split} T &= (-2.3791E + 02) * (60)^0 + (2.2011E + 00) * (60)^1 + (2.3223E - 03) * (60)^2 + \cdots \\ &+ (2.3223E - 03) * (60)^5 = -98.6^\circ C \end{split}$$

Sensor

Diode equation vs. temperature

$$V_{\rm D} = \frac{nkT}{q} \ln \left(\frac{l}{l_{\rm S}} + 1 \right) \approx \frac{nkT}{q} \ln \left(\frac{l}{l_{\rm S}} \right)$$

Where

 $\begin{array}{l} V_{\text{D}} = \text{diode voltage vs. temperature and current} \\ n = \text{diode ideality factor (ranges from 1 to 2)} \\ k = 1.38 \times 10^{-23} \text{ J/K, Boltzmann's constant} \\ T = \text{temperature in Kelvin} \\ q = 1.60 \times 10^{-19} \text{ C, charge of an electron} \\ I = \text{forward diode current in amps} \\ I_{\text{S}} = \text{saturation current} \end{array}$

 $I_S = \alpha T^{(3/n)} exp\left(-\frac{qV_G}{nkT}\right)$

Where

$$\begin{split} I_{s} &= \text{saturation current} \\ \alpha &= \text{constant related to the cross sectional area of the junction} \\ V_{G} &= \text{diode voltage vs. temperature and current} \\ n &= \text{diode ideality factor (ranges from 1 to 2)} \\ k &= 1.38 \times 10^{-23} \text{ J/K, Boltzmann's constant} \\ T &= \text{temperature in Kelvin} \\ q &= 1.60 \times 10^{-19} \text{ C, charge of an electron} \end{split}$$

(95) Diode voltage

(96) Saturation current



Diode voltage versus temperature

Figure 50 shows an example of the temperature drift for a diode. Depending on the characteristics of the diode and the forward current the slope and offset of this curve will change. However, typical diode drift is about $-2mV/^{\circ}C$. A forward drop of about 0.6V is typical for room temperature.

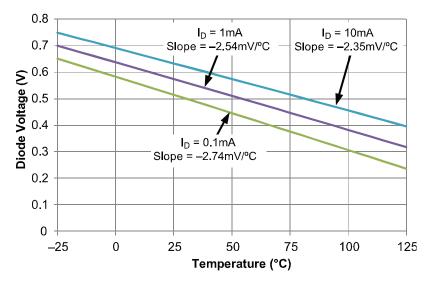


Figure 50: Diode voltage drop vs. temperature

Sensor

Type J thermocouples translating temperature to voltage (ITS-90 standard)

$$V_t = \sum_{i=0}^n c_i \left(T\right)^i$$

(97) Thermoelectric voltage

Where V_T = thermoelectric voltage T = temperature in degrees Celsius c_i = translation coefficients

Table 24: Type J thermocouple	e temperature to	voltage coefficients
-------------------------------	------------------	----------------------

Type J thermocouple temperature to voltage							
	–219°C to 760°C	760℃ to 1,200℃					
c0	0.000000000E+00	2.9645625681E+05					
c1	5.0381187815E+01	-1.4976127786E+03					
c2	3.0475836930E-02	3.1787103924E+00					
c3	-8.5681065720E-05	-3.1847686701E-03					
c4	1.3228195295E-07	1.5720819004E-06					
c5	-1.7052958337E-10	-3.0691369056E-10					
c6	2.0948090697E-13						
c7	-1.2538395336E-16						
c8	1.5631725697E-20						



Type J thermocouples translating voltage to temperature (ITS-90 standard)

$$T = \sum_{i=0}^{n} c_i \left(V_t \right)^i$$

(98) Temperature

Type J thermocouple voltage to temperature								
	–219°C to 0°C	760°C to 1,200°C						
c0	0.00000000E+00	0.00000000E+00	-3.113581870E+03					
c1	1.952826800E-02	1.978425000E-02	3.005436840E-01					
c2	-1.228618500E-06	-2.001204000E-07	-9.947732300E-06					
c3	-1.075217800E-09	1.036969000E-11	1.702766300E-10					
c4	-5.908693300E-13	-2.549687000E-16	-1.430334680E-15					
c5	-1.725671300E-16	3.585153000E-21	4.738860840E-21					
c6	-2.813151300E-20	-5.344285000E-26						
с7	-2.396337000E-24	5.099890000E-31						
c8	-8.382332100E-29							

Table 25: Type J thermocouple voltage to temperature coe	oefficients
--	-------------

Sensor

Type K thermocouples translating temperature to voltage (ITS-90 standard)

$$V_{T} = \sum_{i=0}^{n} c_{i} (T)^{i}$$

$$V_t = \left[\sum_{i=0}^n c_i \left(T\right)^i\right] + \alpha_0 e^{[\alpha_1 (T-126.9686)]^2}$$

- (99) Thermoelectric voltage for T<0°C
- (100) Thermoelectric voltage forT>0°C

Where

V_T = thermoelectric voltage

T = temperature in degrees Celsius

c_i = translation coefficients

 α_0 , α_1 = translation coefficients

	–219°C to 760°C	760°C to 1,200°C
C ₀	0.000000000E+00	-1.7600413686E+01
C 1	3.9450128025E+01	3.8921204975E+01
C ₂	2.3622373598E-02	1.8558770032E-02
C ₃	-3.2858906784E-04	-9.9457592874E-05
C ₄	-4.9904828777E-06	3.1840945719E-07
C 5	-6.7509059173E-08	-5.6072844889E-10
C ₆	-5.7410327428E-10	5.6075059059E-13
C ₇	-3.1088872894E-12	-3.2020720003E-16
C ₈	-1.0451609365E-14	9.7151147152E-20
C ₉	-1.9889266878E-17	-1.2104721275E-23
C ₁₀	-1.6322697486E-20	
α0		1.1859760000E+02
α1		-1.1834320000E-04

Table 26: Type K thermocouple temperature to voltage coefficients



Type K thermocouples translating voltage to temperature (ITS-90 standard)

$$T = \sum_{i=0}^n c_i \left(V_t\right)^i$$

(101) Temperature

	–219°C to 0°C	0°C to 760°C	760°C to 1,200°C
c0	0.0000000E+00	0.0000000E+00	-1.3180580E+02
c1	2.5173462E-02	2.5083550E-02	4.8302220E-02
c2	-1.1662878E-06	7.8601060E-08	-1.6460310E-06
c3	-1.0833638E-09	-2.5031310E-10	5.4647310E-11
c4	-8.9773540E-13	8.3152700E-14	-9.6507150E-16
c5	-3.7342377E-16	-1.2280340E-17	8.8021930E-21
c6	-8.6632643E-20	9.8040360E-22	-3.1108100E-26
c7	-1.0450598E-23	-4.4130300E-26	
c8	-5.1920577E-28	1.0577340E-30	
c9		-1.0527550E-35	

Table 27: Type K thermocouple voltage to temperature coefficients

Sensor

Table 28: Seebeck coefficients for different material

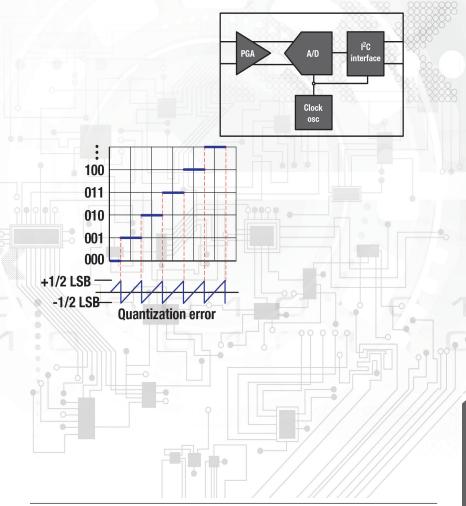
Material	Seebeck coefficient	Material	Seebeck coefficient	Material	Seebeck coefficient
Aluminum	3.5	Gold	6.5	Rhodium	6.0
Antimony	47	Iron	19	Selenium	900
Bismuth	-72	Lead	4.0	Silicon	440
Cadmium	7.5	Mercury	0.6	Silver	6.5
Carbon	3.0	Nichrome	25	Sodium	-2.0
Constantan	-35	Nickel	-15	Tantalum	4.5
Copper	6.5	Platinum	0	Tellurium	500
Germanium	300	Potassium	-9.0	Tungsten	7.5

Note: Units are μ V/°C. All data at temperature of 0°C

• Binary/hex conversions

• A/D and D/A transfer function

- Quantization error
- Signal-to-noise ratio (SNR)
- Signal-to-noise and distortion (SINAD)
- Total harmonic distortion (THD)
- Effective number of bits (ENOB)
- Noise-free resolution and effective resolution

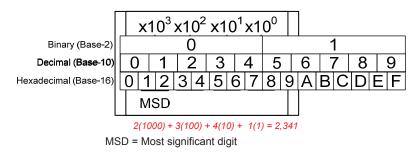


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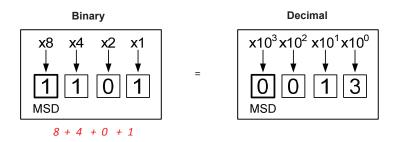
A/D conversion

A/D conversion

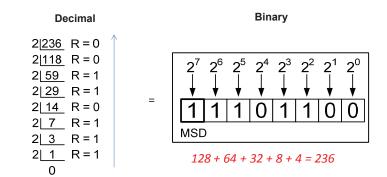
Numbering systems: Binary, decimal, and hexadecimal



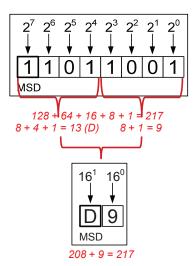
Example conversion: Binary to decimal



Example conversion: Decimal to binary



Example conversion: Binary to hexadecimal

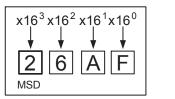


Example Conversion: Hexadecimal to binary

Decimal (Base-10)																
Hexadecimal (Base-16)	0	1	2	3	4	5	6	7	8	9	А	В	С	D	Ε	F

=

Hexadecimal



2(4096) + 6(256) + 10(16) + 16(1) = 9903

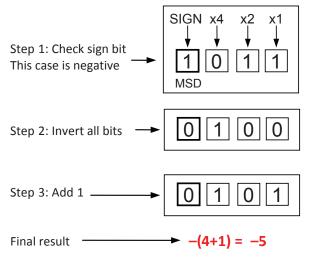
Decimal

A/D conversion

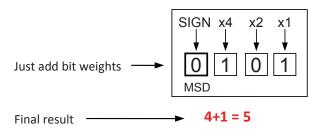
Code	Straight binary	Offset binary	2's complement			
Binary	Decimal value	Decimal value	Decimal value			
11111111	255	127	-1			
11000000	192	64	-64			
1000000	128	0	-128			
01111111	127	-1	127			
01000000	64	-64	64			
0000000	0	-128	0			

Table 29: Different data formats

Converting two's complement to decimal: Negative number example



Converting two's complement to decimal: Positive number example



		Reference voltage										
		1.024 1.25 2.048 2.5										
	8	4 mV	4.88 mV	8 mV	9.76 mV							
	10	1 mV	1.22 mV	2 mV	2.44 mV							
	12	250 µV	305 µV	500 µV	610 µV							
ion	14	52.5 µV	76.3 µV	125 µV	152.5 µV							
Resolution	16	15.6 µV	19.1 µV	31.2 µV	38.14 µV							
Res	18	3.91 µV	4.77 μV	7.81 µV	9.53 µV							
	20	0.98 µV	1.19 µV	1.95 µV	2.384 µV							
	22	244 nV	299 nV	488 nV	596 nV							
	24	61 nV	74.5 nV	122 nV	149 nV							

Table 30: LSB voltage vs. resolution and reference voltage

Table 31: LSB voltage vs. resolution and reference voltage

	Reference voltage									
	3 3.3 4.096									
	8	11.7 mV	12.9 mV	16 mV	19.5 mV					
	10	2.93 mV	3.222 mV	4 mV	4.882 mV					
	12	732 µV	806 µV	1 mV	1.221 mV					
ion	14	183 µV	201 µV	250 µV	305 µV					
Resolution	16	45.77 μV	50.35 µV	62.5 µV	76.29 µV					
Res	18	11.44 µV	12.58 µV	15.6 µV	19.07 µV					
	20	2.861 µV	3.147 μV	3.91 µV	4.768 μV					
	22	715 nV	787 nV	976 nV	1.192 µV					
	24	179 nV	196 nV	244 nV	298 nV					

DAC definitions

Resolution = n	The number of bits used to quantify the output
$Codes = 2^n$	The number of input code combinations
Reference voltage = V _{REF}	Sets the LSB voltage or current size and converter range
$LSB = V_{REF} / 2^n$	The output voltage or current step size of each code
Full-scale code = $2^n - 1$	The largest code that can be written
Full-scale voltage = V _{REF} – 1LSB	Full-scale output voltage of the DAC
Transfer function = $V_{REF} x$ (code/ 2^n)	Relationship between input code and output voltage or current

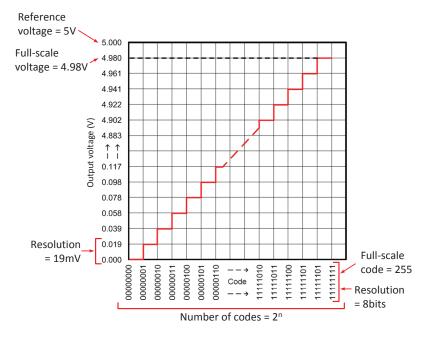


Figure 51: DAC transfer function

ADC definitions

Resolution = n	The number of bits used to quantify the output
Codes = 2 ⁿ	The number of input code combinations
Reference voltage = V _{REF}	Sets the LSB voltage or current size and converter range
$LSB = V_{REF} / (2^n - 1)$	The voltage step size of each code. Note that some topologies may use 2^n as opposed to $2^n - 1$ in the denominator.
Full-scale code = $2^n - 1$	The largest code that can be written.
Full-scale voltage = V _{REF}	Full-scale output voltage of the DAC. Note that the full-scale voltage will differ if the alternative definition for resolution is used.
Transfer function = $V_{REF} x$ (code/ 2^n)	Relationship between input code and output voltage or current

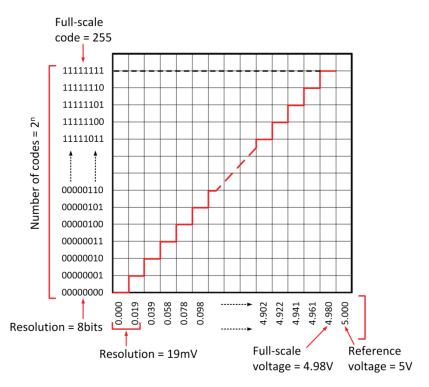


Figure 52: ADC transfer function

Quantization error of ADC

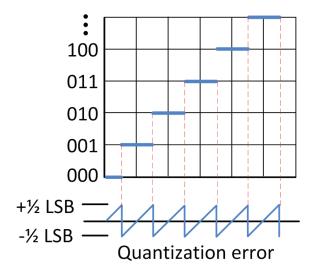


Figure 53: Quantization error of an A/D converter

Quantization error

The error introduced as a result of the quantization process. The amount of this error is a function of the resolution of the converter. The quantization error of an A/D converter is ½ LSB. The quantization error signal the difference between the actual voltage applied and the ADC output (Figure 53). The rms of the quantization signal is $1LSB/\sqrt{12}$

Signal-to-noise ratio (SNR) from quantization noise only

$$MaxRMSSignal = \frac{FSR/2}{\sqrt{2}} = \frac{1LSB \times 2^{N-1}}{\sqrt{2}}$$
(102)

$$RMSNoise = \frac{1LSB}{\sqrt{12}}$$
 from quantization only (103)

$$SNR = \frac{MaxRMSSignal}{RMSNoise} = \frac{1LSB \times 2^{N-1}/\sqrt{2}}{1LSB/\sqrt{12}} = 2^{N-1}\sqrt{6}$$
(104)

$$SNR(dB) = 20\log(SNR) = [20\log(2)]N + 20\log\left(\frac{\sqrt{6}}{2}\right)$$
(105)

$$SNR(dB) \approx 6.02N + 1.76$$
 (106)

Where

 $\label{eq:FSR} \begin{array}{l} \mbox{FSR} = \mbox{full-scale range of the A/D converter} \\ 1LSB = \mbox{the voltage of 1LSB}, \mbox{V}_{REF}/2^n \\ \mbox{N} = \mbox{the resolution of the A/D converter} \\ \mbox{MaxRMSSignal} = \mbox{the rms equivalent of the ADC's full-scale input} \\ \mbox{RMSNoise} = \mbox{the rms noise from quantization} \\ \mbox{SNR} = \mbox{the ratio of rms signal to rms noise} \end{array}$

Example

What is the SNR for an 8-bit A/D converter with 5V reference, assuming only quantization noise?

Answer

 $SNR = 2^{N-1}\sqrt{6} = 2^{8-1}\sqrt{6} = 314$

SNR(dB) = 20log(314) = 49.9 dB

SNR(dB) = 6.02(8) + 1.76 = 49.9 dB

Total harmonic distortion (Vrms)

$$THD = \left(\frac{RMSDistortion}{MaxRMSSignal}\right) = \frac{\sqrt{V_2^2 + V_3^2 + V_4^2 + \dots + V_n^2}}{V_1}$$
(107)
$$THD(dB) = 20log\left(\frac{RMSDistortion}{MaxRMSSignal}\right)$$
(108)

Where

THD = total harmonic distortion, the ratio of the rms distortion to the rms signal RMSDistortion = the rms sum of all harmonic components MaxRMSSignal = the rms value of the input signal V_1 = the fundamental, generally the input signal V_2 , V_3 , V_4 , ..., V_n = harmonics of the fundamental

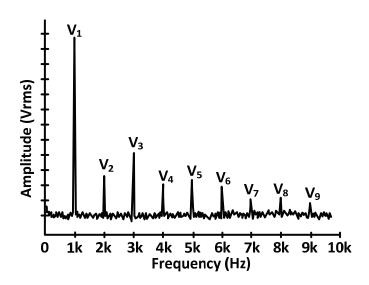


Figure 54: Fundamental and harmonics in Vrms

Total harmonic distortion (dBc)

THD =
$$10 \log \left[10^{\left(\frac{D_2}{10}\right)} + 10^{\left(\frac{D_3}{10}\right)} + 10^{\left(\frac{D_4}{10}\right)} + \dots + 10^{\left(\frac{D_n}{10}\right)} \right]$$
 (109)

Where

THD = total harmonic distortion. The ratio of the rms distortion to the rms signal D_1 = the fundamental, generally the input signal. This is normalized to 0 dBc D_2 , D_3 , D_4 , ... D_n = harmonics of the fundamental measured relative to the fundamental

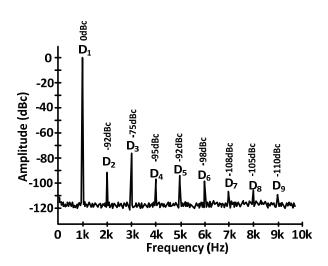


Figure 55: Fundamental and harmonics in dBc

Example

Determine THD for the example above.

Answer

THD =
$$10 \log \left[10^{\left(\frac{-92}{10}\right)} + 10^{\left(\frac{-75}{10}\right)} + 10^{\left(\frac{-95}{10}\right)} + \dots + 10^{\left(\frac{-110}{10}\right)} \right]$$

THD = -74.76 dB

Ac signals

Signal-to-noise and distortion (SINAD) and effective number of bits (ENOB)

$$SINAD(dB) = 20 \log \left(\frac{MaxRMSSignal}{\sqrt{RMSNoise^2 + RMSDistortion^2}} \right)$$
(110)
$$SINAD(dB) = -20 \log \left(\sqrt{10^{\left(\frac{-SNR(dB)}{10}\right)} + 10^{\left(\frac{THD(dB)}{10}\right)}} \right)$$
(111)

$$ENOB = \frac{SINAD(dB) - 1.76dB}{6.02}$$
 (112)

Where

MaxRMSSignal = the rms equivalent of the ADC's full-scale input RMSNoise = the rms noise integrated across the A/D converters RMSDistortion = the rms sum of all harmonic components SINAD = the ratio of the full-scale signal-to-noise ratio and distortion THD = total harmonic distortion. The ratio of the rms distortion to the rms signal. SNR = the ratio of rms signal to rms noise

Example

Calculate the SNR, THD, SINAD and ENOB given the following information: MaxRMSSignal = 1.76 Vrms RMSDistortion = 50 μ Vrms RMSNoise = 100 μ Vrms

Answer

SNR(dB) =
$$20 \log \left(\frac{1.76 \text{ Vrms}}{100 \,\mu \text{Vrms}} \right) = 84.9 \text{ dB}$$

THD(dB) = $20 \log \left(\frac{50 \,\mu \text{Vrms}}{1.76 \text{ Vrms}} \right) = -90.9 \text{ dB}$

SINAD(dB) =
$$20 \log \left(\frac{1.76 \text{V rms}}{\sqrt{(100 \ \mu \text{V rms})^2 + (50 \ \mu \text{V rms})^2}} \right) = 83.9 \text{ dB}$$

SINAD(dB) = $-20 \log \left(\sqrt{10^{\left(\frac{-83.9 \text{ dB}}{10} \right)} + 10^{\left(\frac{-90.9 \text{ dB}}{10} \right)}} \right) = 83.9 \text{ dB}$
ENOB = $\frac{83.9 \text{ dB} - 1.76 \text{ dB}}{6.02} = 13.65$

Dc signals

Noise free resolution and effective resolution

NoiseFreeResolution =
$$\log_2\left(\frac{2^N}{\text{PeaktoPeakNoiseinLSB}}\right)$$
 (113)

EffectiveResolution =
$$\log_2\left(\frac{2^N}{\text{rmsNoiseinLSB}}\right)$$
 (114)

$$PeaktoPeakNoiseinLSB \approx 6.6 \times rmsNoiseinLSB$$
(115)

EffectiveResolution \approx NoiseFreeResolution + 2.7 (116)

Note: The maximum *effective resolution* is never greater than the ADC resolution. For example, a 24-bit converter cannot have an effective resolution greater than 24 bits.

Example

What is the noise-free resolution and effective resolution for a 24-bit converter assuming the peak-to-peak noise is 7 LSBs?

Answer

NoiseFreeResolution = $\log_2\left(\frac{2^{24}}{7}\right) = 21.2$

EffectiveResolution =
$$\log_2\left(\frac{2^{24}}{\frac{7}{6.6}}\right) = 23.9$$

EffectiveResolution = 21.2 + 2.7 = 23.9

A/D conversion

Time Constant = τ = R C

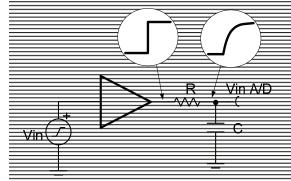


Figure 56: Settling time for RC circuit-related to A/D converters

Table 32: Conversion accuracy achieved after a specified time

Settling time in		Settling time in	
time constants	Accuracy in	time constants	Accuracy in
(N _{TC})	bits	(N _{TC})	bits
1	1.44	10	14.43
2	2.89	11	15.87
3	4.33	12	17.31
4	5.77	13	18.76
5	7.21	14	20.20
6	8.66	15	21.64
7	10.10	16	23.08
8	11.54	17	24.53
9	12.98	18	25.97

 $N = \log_2(e^{-N_{TC}})$

(117)

Where

N = the number of bits of accuracy the RC circuit has settled to after N_{1C} number of time constants

ume constants.

N_{TC} = the number of RC time constants

Table 33: Time	e required to settle	to a specified	conversion accura	юу
	Settling time in		Settling time in	
Accuracy	time constants	Accuracy	time constants	
in bits (N)	(N _{TC})	in bits (N)	(N _{TC})	
8	5.55	17	11.78	
9	6.24	18	12.48	
9 10 11	6.93	19	13.17	
11	7.62	20	13.86	
12	8.32	21	14.56	
13	9.01	22	15.25	
14	9.70	23	15.94	
15	10.40	24	16.64	
16	11.09	25	17.33	

 $N_{TC} = \ln(2^N)$

(118)

Where

 N_{TC} = the number of time constants required to achieve N bits of settling

N = the number of bits of accuracy

Notes	

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